

P-Channel 100 V (D-S) MOSFET

PRODUCT SUMMARY

V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)	Q_g (Typ.)
- 100	0.043 at $V_{GS} = - 10$ V	- 37	54 nC
	0.048 at $V_{GS} = - 4.5$ V	- 35	

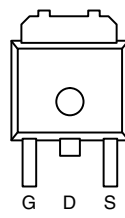
FEATURES

- TrenchFET® Power MOSFET
- Material categorization:
For definitions of compliance please see
www.vishay.com/doc?99912



RoHS
COMPLIANT
HALOGEN
FREE

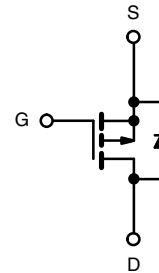
TO-252



Top View

Drain Connected to Tab

Ordering Information:
SUD50P10-43L-GE3 (Lead (Pb)-free and Halogen-free)



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS ($T_A = 25$ °C, unless otherwise noted)

Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V _{DS}	- 100	V	
Gate-Source Voltage		V _{GS}	± 20		
Continuous Drain Current (T _J = 150 °C) ^b	T _C = 25 °C	I _D	- 36.4	A	
	T _C = 70 °C		- 29.1		
	T _A = 25 °C		- 9 ^{b, c}		
	T _A = 70 °C		- 7.2 ^{b, c}		
Pulsed Drain Current		I _{DM}	- 40		
Continuous Source Current (Diode Conduction)	T _C = 25 °C	I _S	- 50 ^a		
	T _A = 25 °C		- 5.75 ^{b, c}		
Avalanche Current	L = 0.1 mH	I _{AS}	- 35		
Single Pulse Avalanche Energy		E _{AS}	61	mJ	
Maximum Power Dissipation	T _C = 25 °C	P _D	113.6	W	
	T _C = 70 °C		72.7		
	T _A = 25 °C		6.9 ^{b, c}		
	T _A = 70 °C		4.4 ^{b, c}		
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150	°C	

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Junction-to-Ambient ^a	R_{thJA}	15	18	°C/W
		40	50	
Junction-to-Case (Drain)	R_{thJC}	0.85	1.1	

Notes:

- Package limited.
- Surface mounted on 1" x 1" FR4 board.
- $t = 10$ s.
- Maximum under steady state conditions is 50 °C/W.

SPECIFICATIONS ($T_J = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = - 250 μA	- 100			V
V _{DS} Temperature Coefficient	ΔV _{DS} /T _J	I _D = - 250 μA		- 109		mV/°C
V _{GS(th)} Temperature Coefficient	ΔV _{GS(th)} /T _J			5.9		
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = - 250 μA	- 1		- 3	V
Gate-Source Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V			± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = - 100 V, V _{GS} = 0 V			- 1	μA
		V _{DS} = - 100 V, V _{GS} = 0 V, T _J = 55 °C			- 10	
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≥ 5 V, V _{GS} = - 10 V	- 40			A
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 10 V, I _D = - 9.2 A		0.036	0.043	Ω
		V _{GS} = - 4.5 V, I _D = - 7.7 A		0.040	0.048	
Forward Transconductance ^a	g _{fs}	V _{DS} = - 15 V, I _D = - 9.2 A		38		S
Dynamic ^b						
Input Capacitance	C _{iss}	V _{DS} = - 50 V, V _{GS} = 0 V, f = 1 MHz		4600		pF
Output Capacitance	C _{oss}			230		
Reverse Transfer Capacitance	C _{rss}			175		
Total Gate Charge	Q _g	V _{DS} = - 50 V, V _{GS} = - 10 V, I _D = - 9.2 A		106	160	nC
		V _{DS} = - 50 V, V _{GS} = - 4.5 V, I _D = - 9.2 A		54	81	
Gate-Source Charge	Q _{gs}			14		
Gate-Drain Charge	Q _{gd}			26		
Gate Resistance	R _g	f = 1 MHz		4		Ω
Turn-On Delay Time	t _{d(on)}	V _{DD} = - 50 V, R _L = 6.5 Ω I _D ≅ - 7.7 A, V _{GEN} = - 10 V, R _g = 1 Ω		15	25	ns
Rise Time	t _r			20	30	
Turn-Off Delay Time	t _{d(off)}			110	165	
Fall Time	t _f			100	150	
Turn-On Delay Time	t _{d(on)}	V _{DD} = - 50 V, R _L = 6.5 Ω I _D ≅ - 7.7 A, V _{GEN} = - 4.5 V, R _g = 1 Ω		42	65	ns
Rise Time	t _r			160	240	
Turn-Off Delay Time	t _{d(off)}			100	150	
Fall Time	t _f			100	150	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C			- 50	A
Pulse Diode Forward Current ^a	I _{SM}				- 40	
Body Diode Voltage	V _{SD}	I _S = - 7.7 A		- 0.8	- 1.2	V
Body Diode Reverse Recovery Time	t _{rr}	I _F = - 7.7 A, dI/dt = 100 A/μs, T _J = 25 °C		60	90	ns
Body Diode Reverse Recovery Charge	Q _{rr}			150	225	nC
Reverse Recovery Fall Time	t _a			46		ns
Reverse Recovery Rise Time	t _b			14		

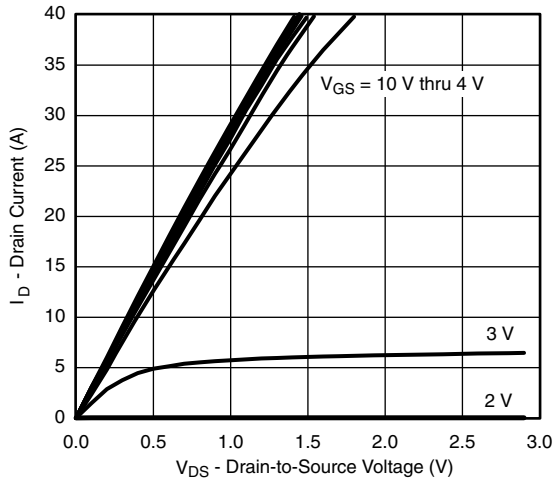
Notes:

a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

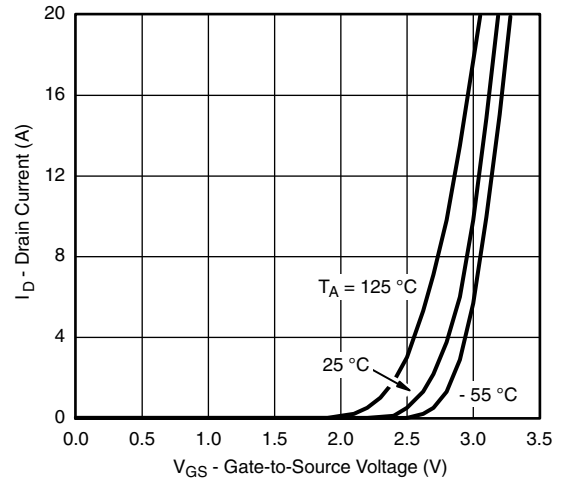
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

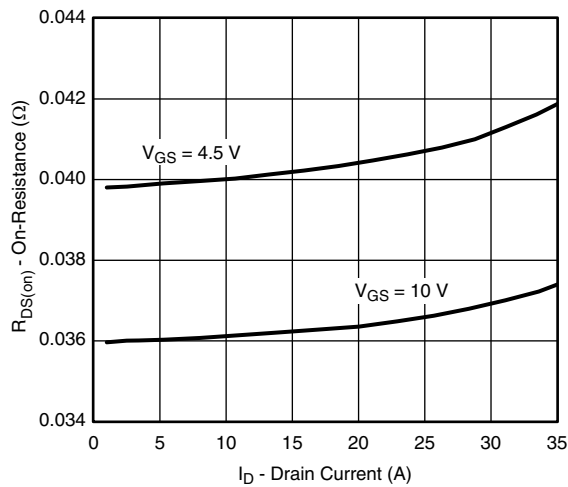
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



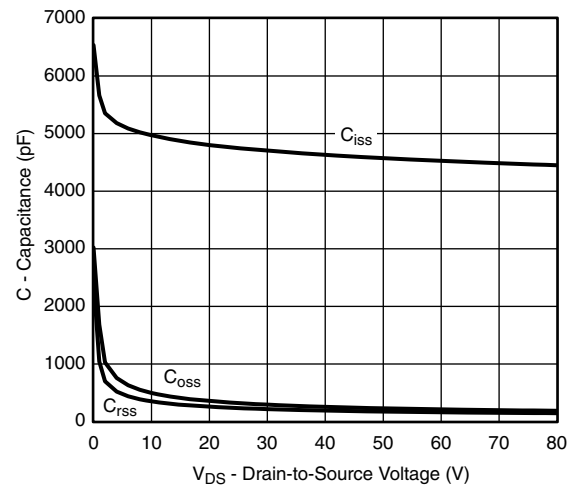
Output Characteristics



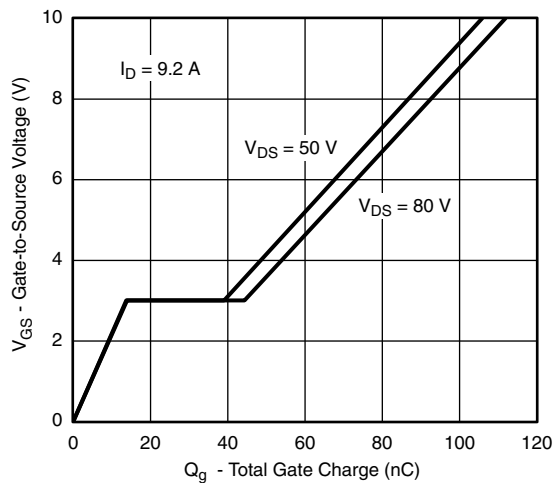
Transfer Characteristics



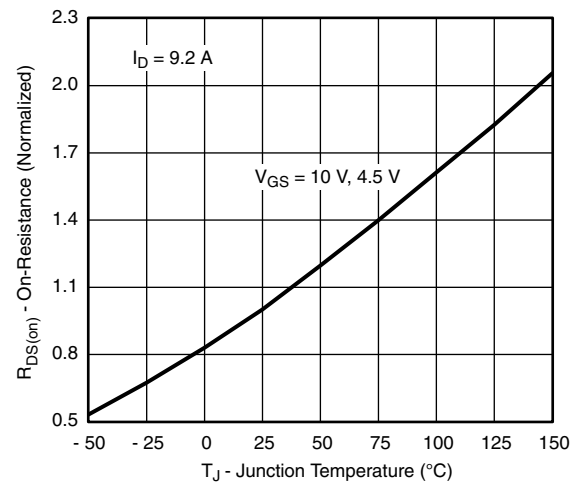
On-Resistance vs. Drain Current and Gate Voltage



Capacitance

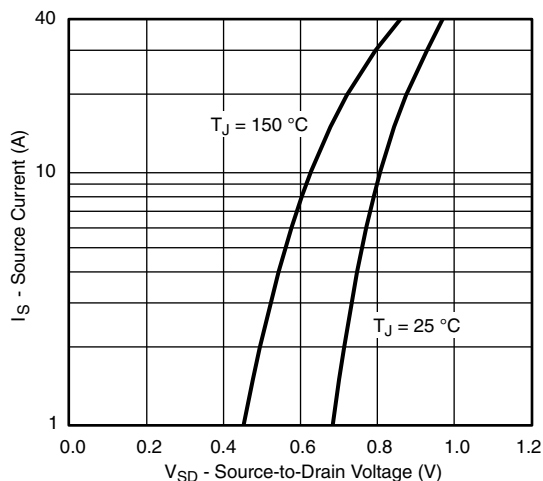


Gate Charge

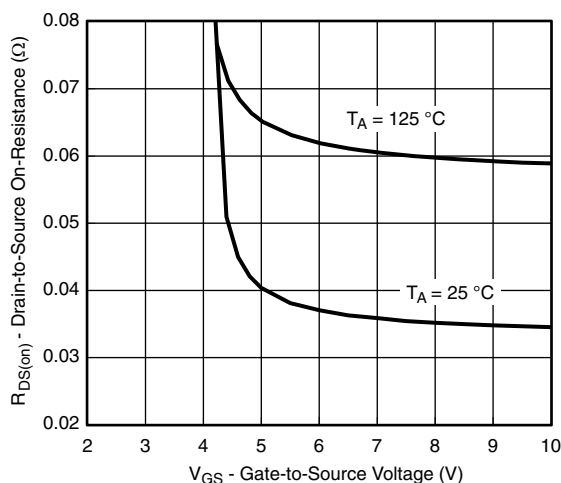


On-Resistance vs. Junction Temperature

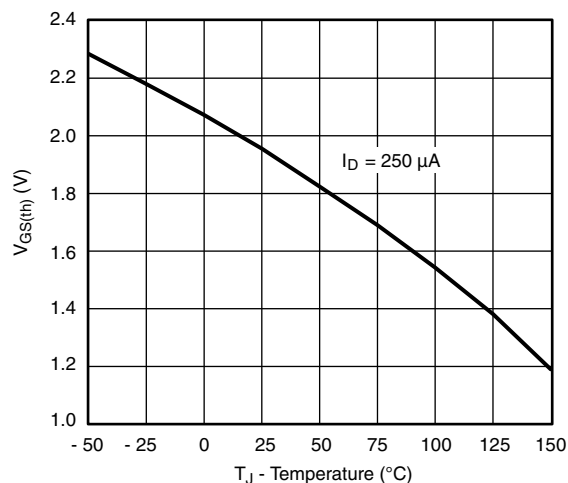
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



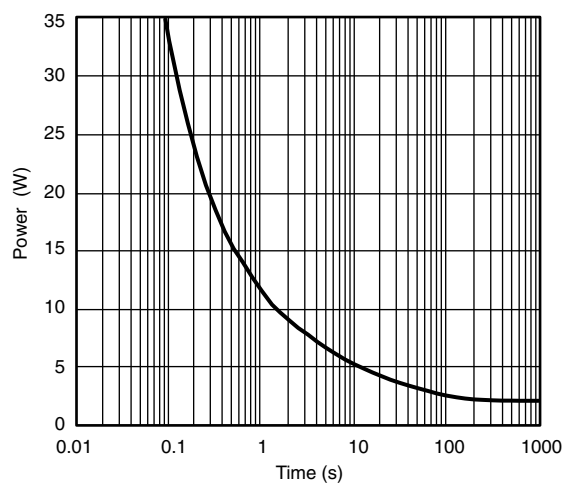
Source-Drain Diode Forward Voltage



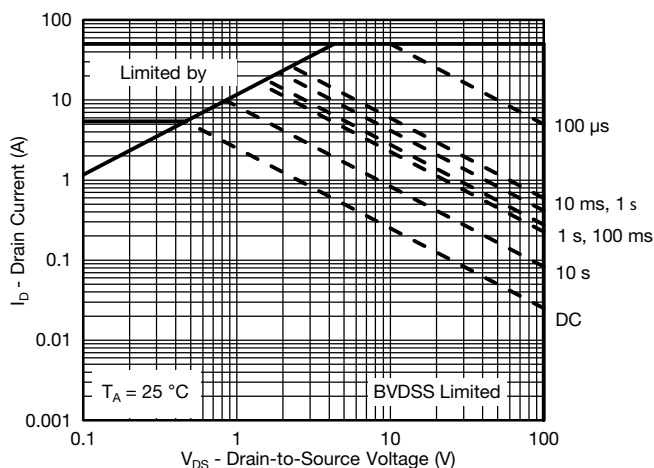
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



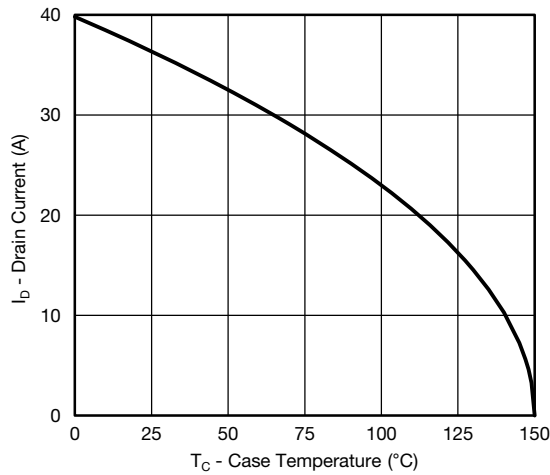
Single Pulse Power, Junction-to-Ambient



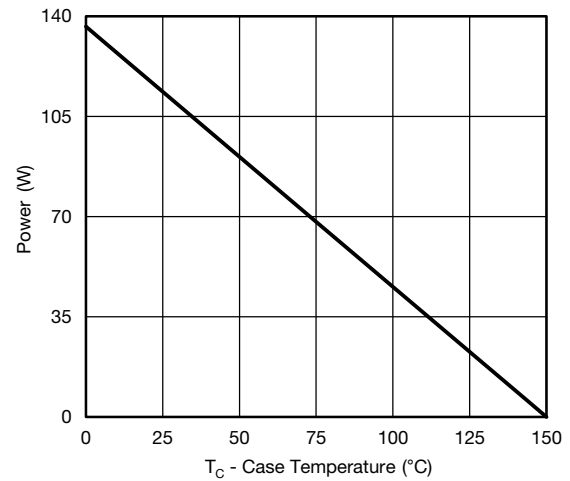
* $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

Safe Operating Area, Junction-to-Ambient

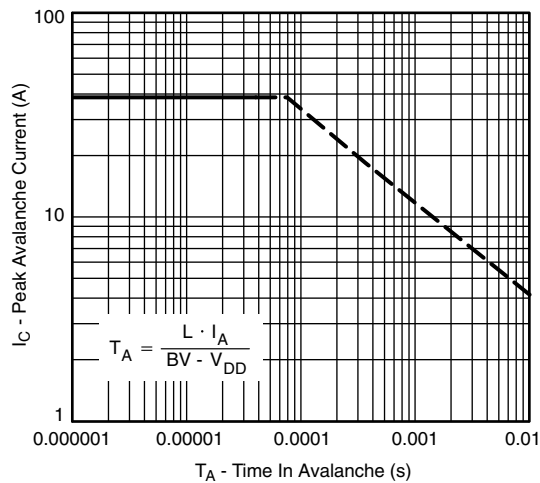
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Current Derating*

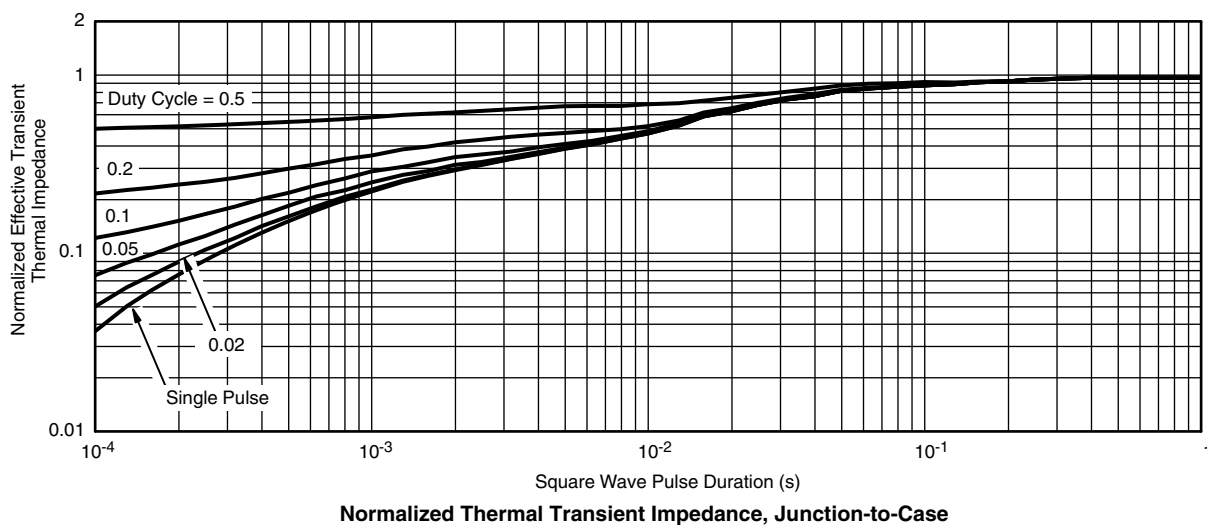
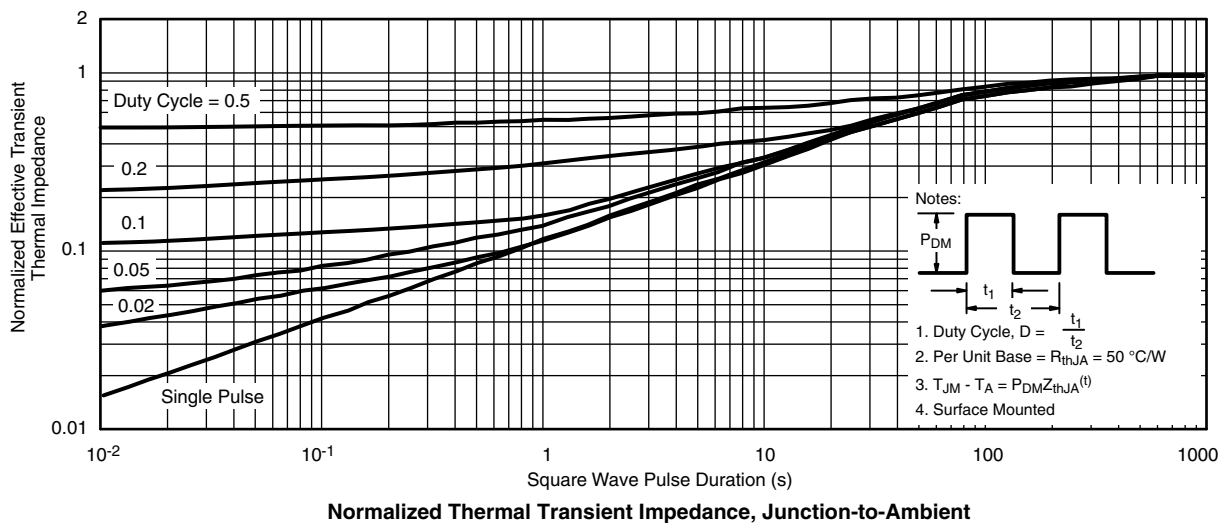


Single Pulse Power, Junction-to-Ambient



Single Pulse Avalanche Capability

* The power dissipation P_D is based on $T_{J(max)} = 150\text{ °C}$, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

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TO-252AA Case Outline

VERSION 1: FACILITY CODE = Y



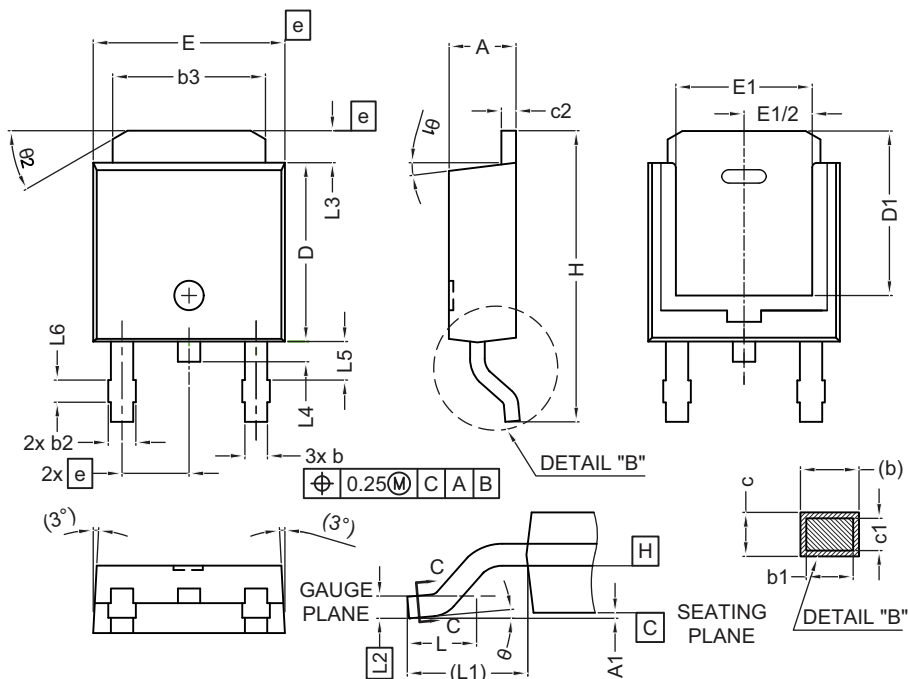
	MILLIMETERS	
DIM.	MIN.	MAX.
A	2.18	2.38
A1	-	0.127
b	0.64	0.88
b2	0.76	1.14
b3	4.95	5.46
C	0.46	0.61
C2	0.46	0.89
D	5.97	6.22
D1	4.10	-
E	6.35	6.73
E1	4.32	-
H	9.40	10.41
e	2.28 BSC	
e1	4.56 BSC	
L	1.40	1.78
L3	0.89	1.27
L4	-	1.02
L5	1.01	1.52

Note

- Dimension L3 is for reference only



VERSION 2: FACILITY CODE = N



DIM.	MILLIMETERS	
	MIN.	MAX.
A	2.18	2.39
A1	-	0.13
b	0.65	0.89
b1	0.64	0.79
b2	0.76	1.13
b3	4.95	5.46
c	0.46	0.61
c1	0.41	0.56
c2	0.46	0.60
D	5.97	6.22
D1	5.21	-
E	6.35	6.73
E1	4.32	-
e	2.29 BSC	
H	9.94	10.34

DIM.	MILLIMETERS	
	MIN.	MAX.
L	1.50	1.78
L1	2.74 ref.	
L2	0.51 BSC	
L3	0.89	1.27
L4	-	1.02
L5	1.14	1.49
L6	0.65	0.85
theta	0°	10°
theta1	0°	15°
theta2	25°	35°

Notes

- Dimensioning and tolerance confirm to ASME Y14.5M-1994
- All dimensions are in millimeters. Angles are in degrees
- Heat sink side flash is max. 0.8 mm
- Radius on terminal is optional

ECN: E19-0649-Rev. Q, 16-Dec-2019
DWG: 5347

RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads
Dimensions in Inches/(mm)

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